

**IN THE SPECIFICATION:**

Please rewrite paragraph [0052] to read as follows:

--Referring to Figures 4(c)-(d), a single low energy implant (~~please enter the energy of the implant~~) is introduced via ion implantation to form a dopant region 20 including deep source/drain regions and shallow source/drain extensions [[20]]. Implant energies for forming the dopant region 20 include ranges similar for forming source/drain regions ~~are~~ typical[ly;]] ranges are from about 1 keV to about 5 keV, preferably about 3 keV, for arsenic; from about 1 keV to about 7 keV, preferably about 4 keV, for BF<sub>2</sub>; and from 1 keV to about 2 keV, preferably about 1 keV, for boron. Following the single low energy implant, an activation anneal is conducted at approximately 850°C, more preferably at about 1000°C as depicted in Figure 3(d). Although boron is preferred, other types of Group III elements may be utilized for producing PFET devices. --

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